

## -200V P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ◇ Advanced TRENCH cell design
- ◇ Low Gate Charge
- ◇ Low On-Resistance
- ◇ RoHS and Halogen-Free Compliant
- ◇ 100%  $\Delta V_{DS}$  & UIS & Rg Tested

#### 1.2 Applications

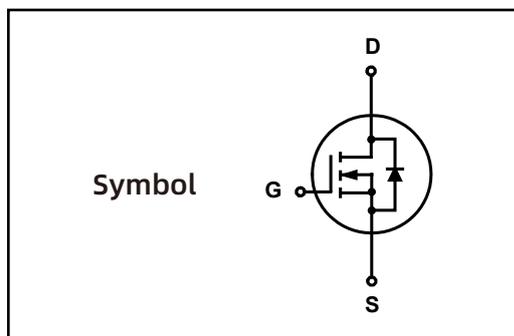
- ◇ DC-DC Converter
- ◇ Drones
- ◇ Motor drivers
- ◇ Light electric vehicles

#### 1.3 Quick reference

- ◇  $BV \cong -200\text{ V}$
- ◇  $P_{\text{tot}} \cong 144\text{ W}$
- ◇  $I_D \cong -14\text{ A}$
- ◇  $R_{DS(\text{ON})} \cong 490\text{ m}\Omega @ V_{GS} = -10\text{ V}$



### 2. Pin Description



### 3.Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit	Note
$V_{DS}$	Drain-Source Voltage	$T_c = 25\text{ }^\circ\text{C}$	-	-200	V	-
$V_{GS}$	Gate-Source Voltage	$T_c = 25\text{ }^\circ\text{C}$	-	$\pm 20$	V	-
$I_D^*$	Drain Current ( DC )	$T_c = 25\text{ }^\circ\text{C}, V_{GS} = -10\text{ V}$	-	-14	A	Fig.2
		$T_c = 100\text{ }^\circ\text{C}, V_{GS} = -10\text{ V}$	-	-9	A	
$I_{DM}^{**},^{***}$	Drain Current ( Pulsed )	$T_c = 25\text{ }^\circ\text{C}, V_{GS} = -10\text{ V}$	-	-17	A	-
$P_{tot}$	Drain power dissipation	$T_c = 25\text{ }^\circ\text{C}$	-	144	W	Fig.1
		$T_c = 100\text{ }^\circ\text{C}$	-	57	W	
$T_{stg}$	Storage Temperature		-55	150	$^\circ\text{C}$	-
$T_j$	Junction Temperature		-	150	$^\circ\text{C}$	-
$I_s$	Continuous-Source Current	$T_c = 25\text{ }^\circ\text{C}$	-	-14	A	-
$E_{AS}^*$	Single Pulsed Avalanche Energy	$V_{DD} = -200\text{ V}, L = 0.1\text{ mH}$	-	51.2	mJ	Fig.19

### 4.Thermal Characteristics

$R_{\theta JA}^*$	Thermal Resistance- Junction to Ambient	-	34	$^\circ\text{C}/\text{W}$	Fig.16
$R_{\theta JC}^*$	Thermal Resistance- Junction to Case	-	0.87		

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$
- \*\* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- \*\*\* limited by bonding wire

### 5.Marking Information

Product Name	Package	Reel size	Tape width	Quantity	Note
LN6R80P200J	TO-252	330mm	16mm	2500	

Note: COMTECH defines “ Green ” as lead-free ( RoHS compliant ) and halogen free ( Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C )

## 6. Electrical Characteristics ( $T_A=25^\circ$ Unless Otherwise Noted )

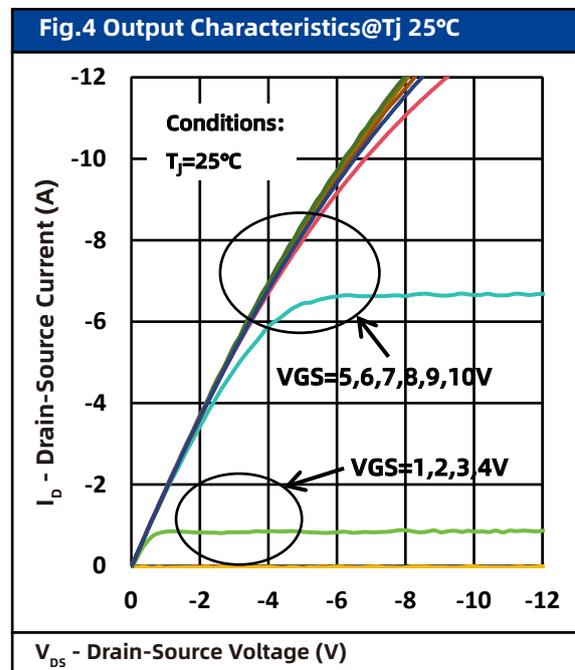
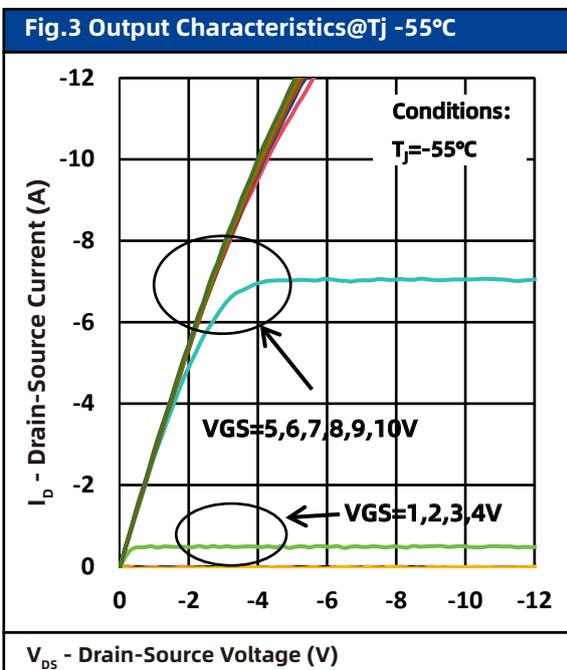
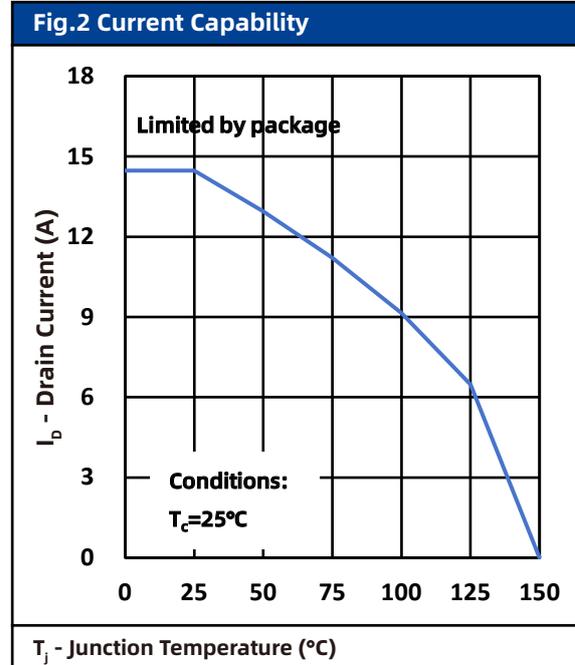
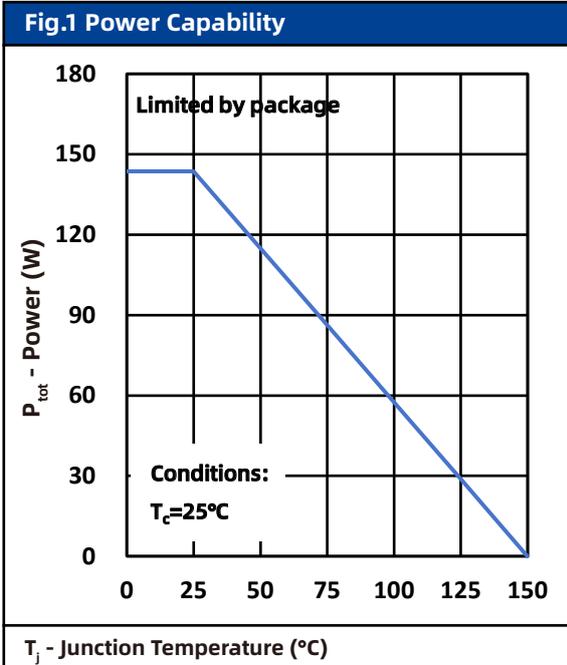
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	Note
<b>Static Characteristics</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = -250\ \mu\text{A}$	-200	-	-	V	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = -250\ \mu\text{A}$	-2	-	-4	V	
$I_{DSS}$	Drain Leakage Current	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$	
$I_{GSS}$	Gate Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA	
$R_{DS(on)}^a$	On-State Resistance	$V_{GS} = -10\text{ V}, I_{DS} = -10\text{ A}$	-	480	490	m $\Omega$	Fig.8
<b>Diode Characteristics</b>							
$V_{SD}^a$	Diode Forward Voltage	$I_{SD} = -10\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.3	V	Fig.7
$t_{rr}$	Reverse Recovery Time	$I_{DS} = -10\text{ A}, V_{GS} = 0\text{ V}$	-	40	-	nS	Fig.20
$Q_{rr}$	Reverse Recovery Charge	$dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	28	-	nC	
<b>Dynamic Characteristics<sup>b</sup></b>							
$C_{ISS}$	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = -100\text{ V}$ Frequency = 1 MHz	-	1241	-	pF	Fig.10
$C_{OSS}$	Output Capacitance		-	93	-		
$C_{rSS}$	Reverse Transfer Capacitance		-	27	-		
$R_G$	Gate Resistance	F= 1 MHz	-	3.5	-	$\Omega$	
$t_d(on)$	Turn-on Delay Time	$V_{DS} = -100\text{ V}, V_{GS} = -10\text{ V},$ $R_G=2.7\ \Omega, R_L = 200\ \mu\text{H},$ $I_{DS} = -10\text{ A}$	-	9.2	-	nS	Fig.18
$t_r$	Turn-on Rise Time		-	47	-		
$t_d(off)$	Turn-off Delay Time		-	22	-		
$t_f$	Turn-off Fall Time		-	12	-		
$dv/dt$	Peak Diode Recovery		-	1.707	-		
$di/dt$	Peak Diode Recovery	-	968	-	A/ $\mu\text{s}$		

Notes :

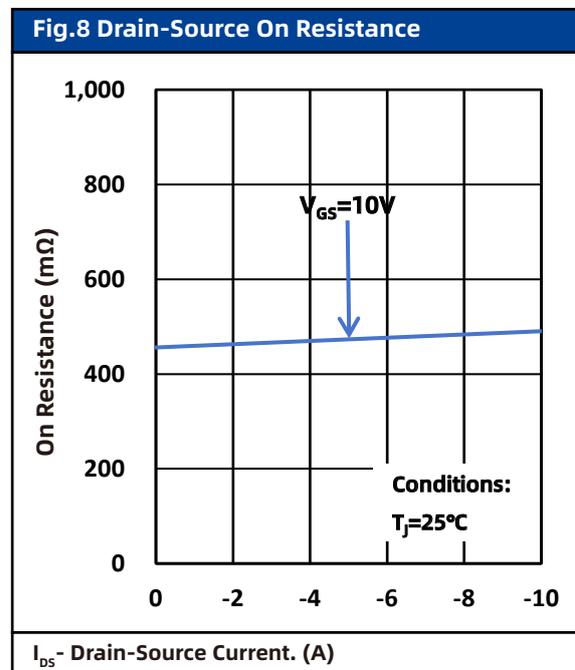
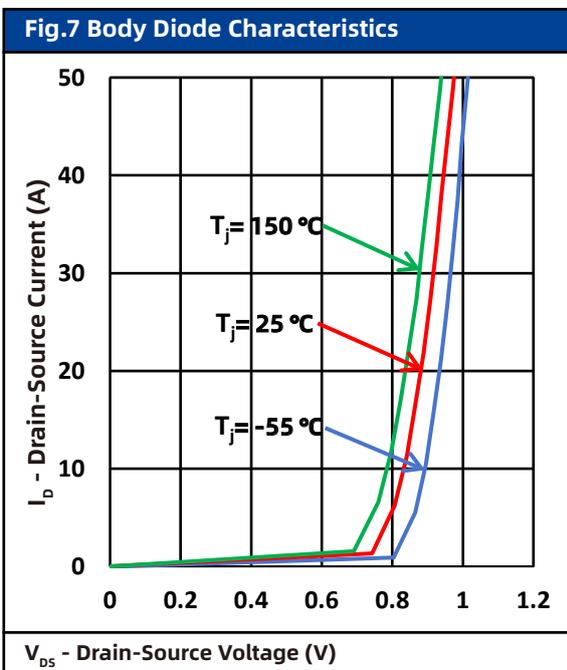
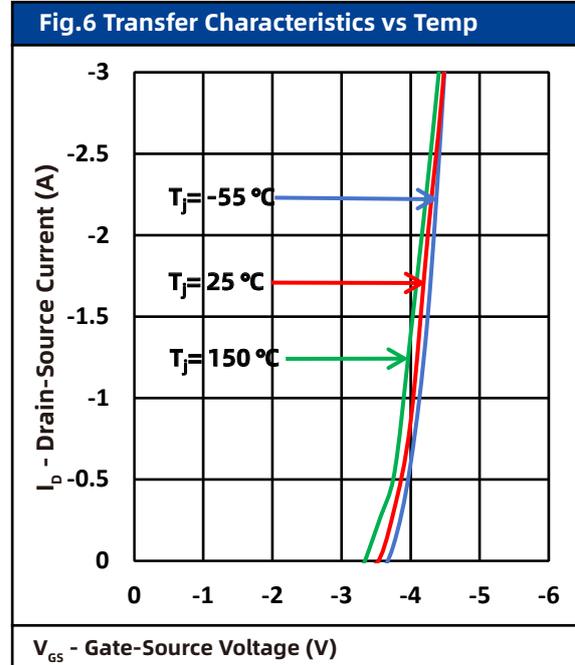
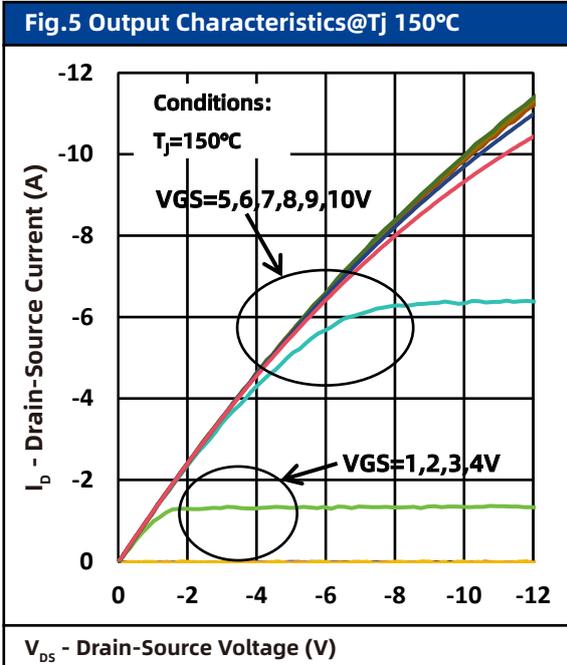
a : Pulse test ; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ 

b : Guaranteed by design, not subject to production testing

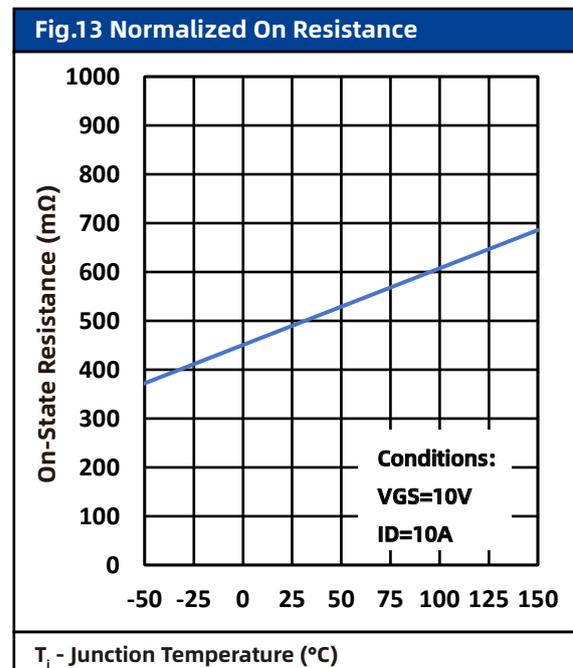
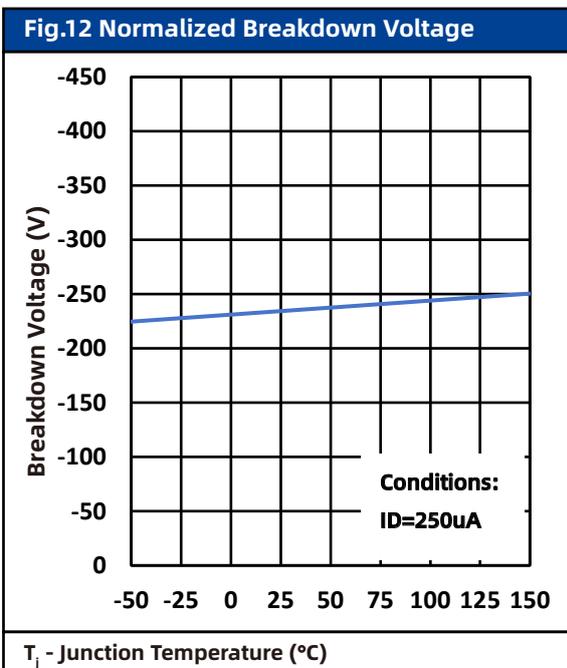
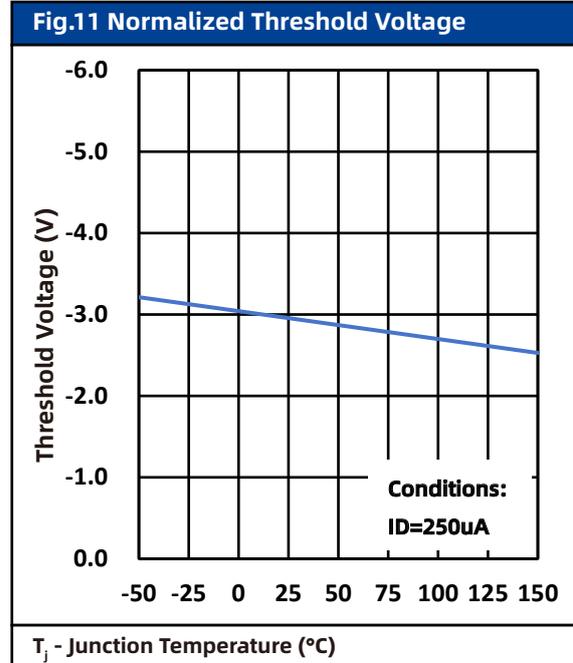
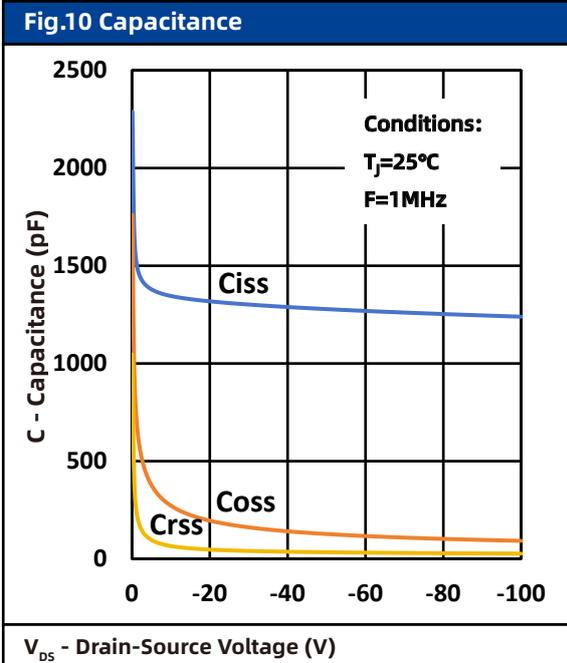
## 7. Typical Characteristics



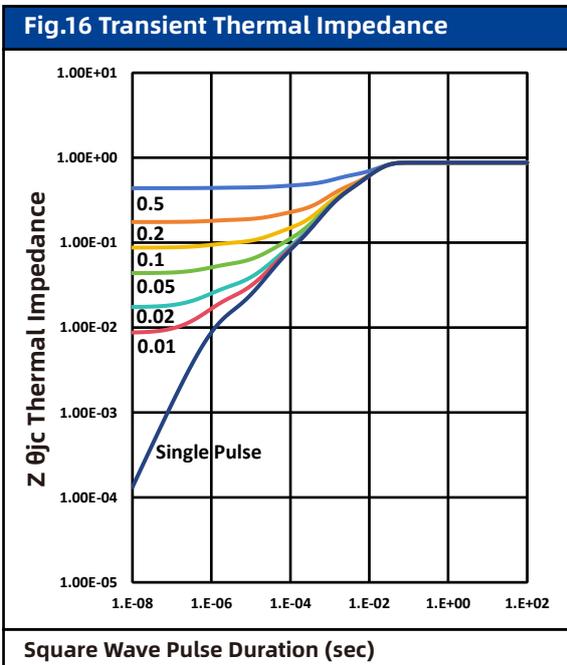
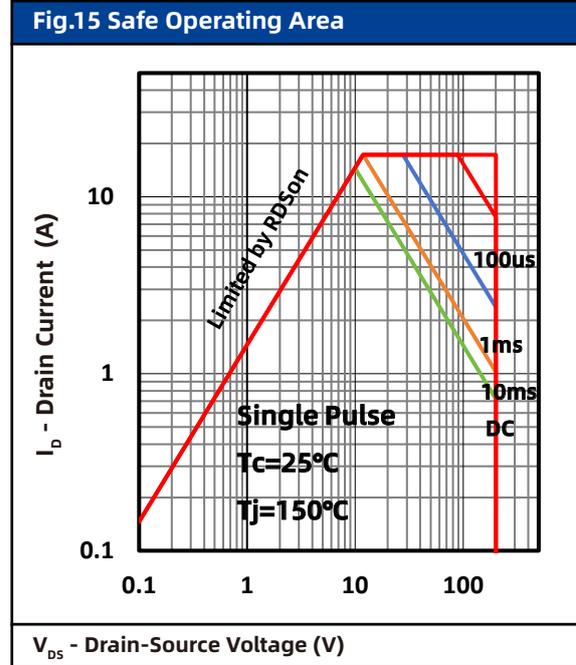
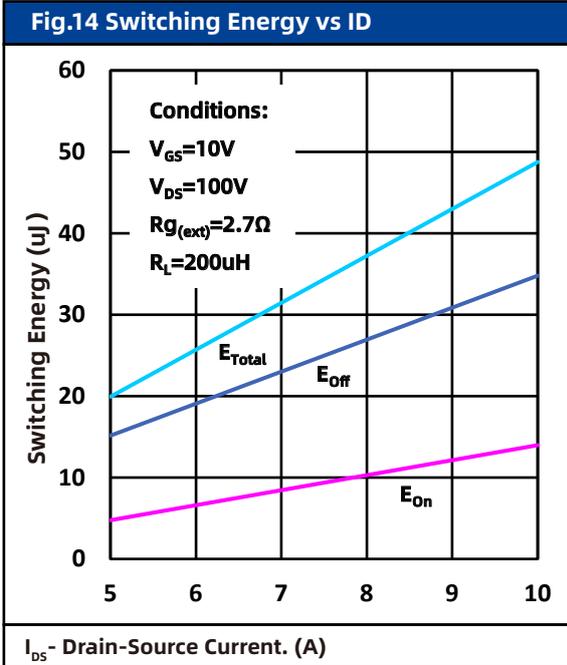
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Fig.17 Gate Charge Test Circuit & Waveform

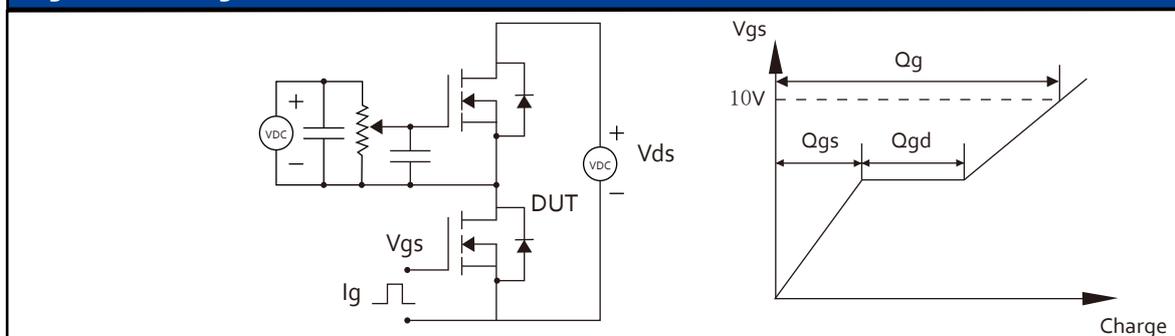


Fig.18 Resistive Switching Test Circuit & Waveforms

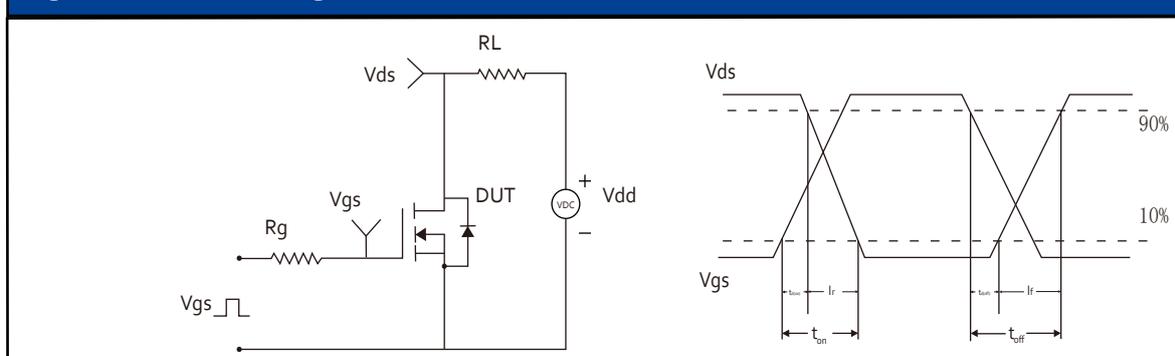


Fig.19 Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

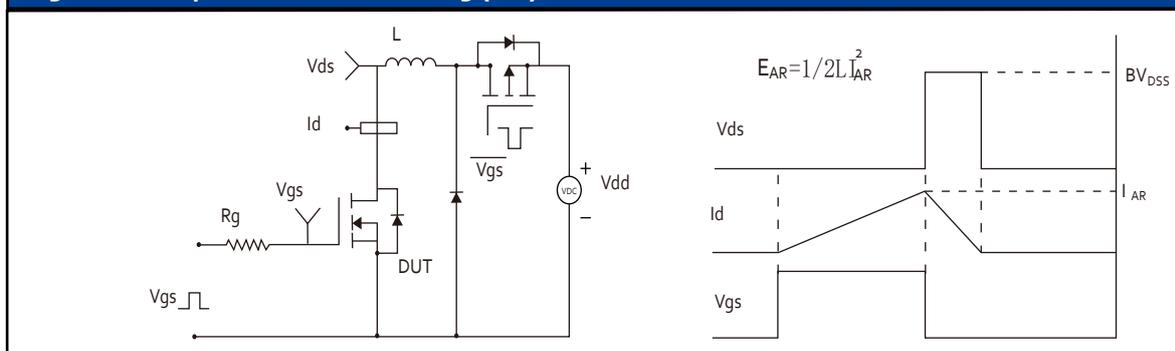
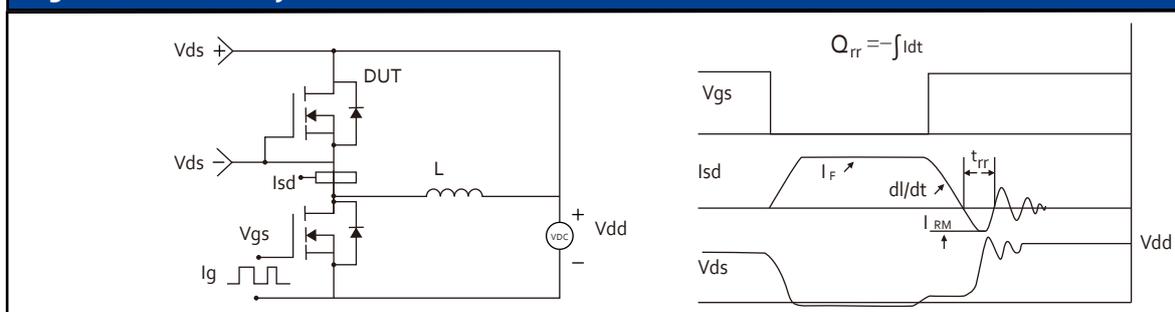
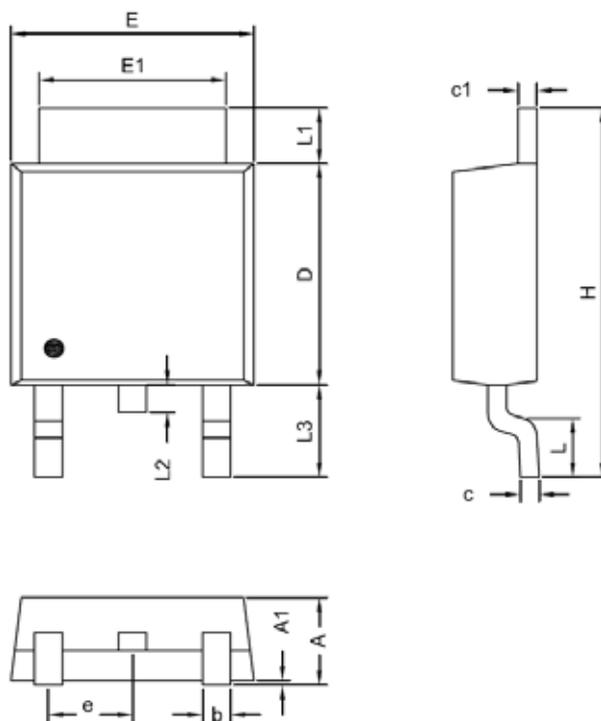


Fig.20 Diode Recovery Test Circuit & Waveforms



## 8. Package Dimensions

### TO-252 Package



Symbol	Unit : mm		Unit : inch	
	MIN	MAX	MIN	MAX
A	2.080	2.500	0.082	0.098
A1	0.000	0.250	0.000	0.010
D	5.300	6.400	0.209	0.252
E	6.100	6.850	0.240	0.270
E1	4.676	5.650	0.184	0.222
c	0.400	0.650	0.016	0.026
c1	0.400	0.650	0.016	0.026
b	0.500	1.000	0.020	0.039
e	2.090	2.500	0.082	0.098
L	1.000	1.800	0.039	0.071
L1	0.700	1.800	0.028	0.071
L2	0.500	1.200	0.020	0.047
L3	2.400	3.070	0.094	0.121
H	9.000	10.700	0.354	0.421

## 9. Record of Document amendment

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版权说明：镭诺电子（宁波）有限公司  
联系电话：4008887385

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修改记录：  
1.初版发行